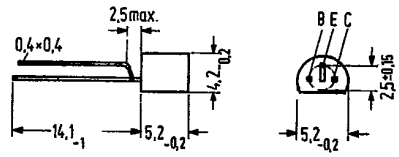
PNP Silicon Planar Transistor — BF 926

BF 926 is an epitaxial PNP silicon planar transistor in TO 92 plastic package (10 A 3 DIN 41868). The transistor is intended for use in VHF oscillator stages, in particular for driving MOS mixer stages.

Type	Ordering code
BF 926	Q62702-F 678



Approx. weight 0.25 g — Dimensions in mm

Maximum ratings

Collector-emitter voltage	$-V_{CEO}$	30	V
Collector-base voltage	$-V_{CBO}$	40	V
Emitter-base voltage	$-V_{EBO}$	4	V
Collector current	$-I_C$	25	mA
Emitter current	$-I_E$	30	mA
Junction temperature	T_j	150	°C
Storage temperature range	T_{stg}	–55 to +150	°C
Total power dissipation (T_{amb} = 45 °C)	P_{tot}	300	mW

Thermal resistance

Junction to ambient air	R_{thJA}	<350	K/W

Static characteristics (T_{amb} = 25 °C)

Collector cutoff current ($-V_{CB}$ = 20 V)	$-I_{CBO}$	<60	nA
Collector-emitter breakdown voltage ($-I_C$ = 2 mA)	$-V_{CEO}$	>30	V
Collector-base breakdown voltage ($-I_C$ = 10 µA)	$-V_{CBO}$	>40	V
Emitter-base breakdown voltage ($-I_E$ = 10 µA)	$-V_{EBO}$	>4	V
DC current gain ($-I_C$ = 1 mA; $-V_{CE}$ = 10 V)	h_{FE}	80 (>30)	–

Dynamic characteristics (T_{amb} = 25 °C)

Transition frequency ($-I_C$ = 5 mA; $-V_{CE}$ = 10 V; f = 100 MHz)	f_T	600	MHz
Reverse transfer capacitance ($-V_{CB}$ = 10 V; $-I_C$ = 5 mA; f = 1 MHz)	$-C_{12e}$	0.6	pF
Output capacitance ($-I_E$ = 0; $-V_{CB}$ = 10 V; f = 1 MHz)	C_{OB}	0.8	pF
Input capacitance ($-V_{EBO}$ = 0.15 V; NF = 1 MHz)	C_{EBO}	2	pF